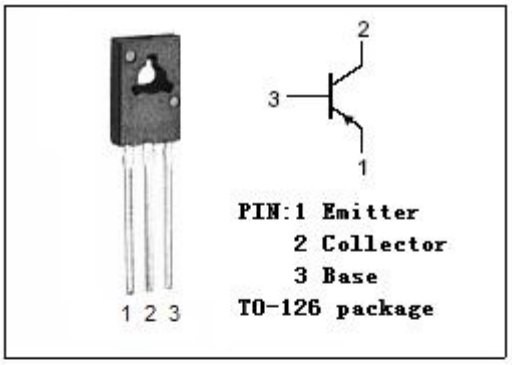
isc Silicon PNP Power Transistor — 2SB986

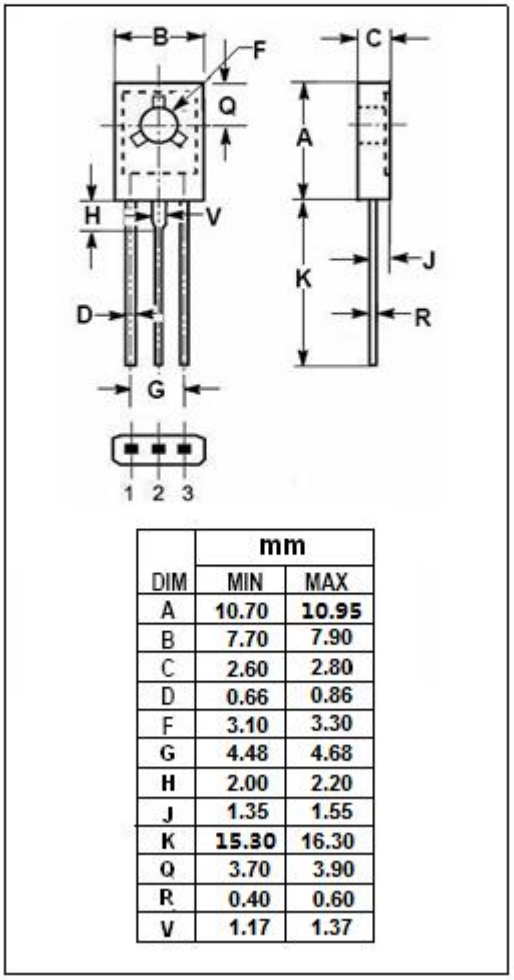
DESCRIPTION

- High Collector Current-I_C= -4.0A
- Low Saturation Voltage -
  : $V_{CE(sat)}$= -0.5V(Max)@ I_C= -2A, I_B= -0.1A
- Good Linearity of h_{FE}
- Complement to Type 2SD1348
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for power supplies, relay drivers, lamp drivers, electrical equipment applications.



DIM	mm MIN	mm MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-4	A
I_{CP}	Collector Current-Pulse	-6	A
P_C	Collector Power Dissipation @ T_a=25℃	1.2	W
	Collector Power Dissipation @ T_C=25℃	10	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -10 μ A; I_E= 0	-60			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -1mA; R_{BE}= ∞	-50			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -10 μ A; I_C= 0	-6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -2.0A; I_B= -0.1A			-0.7	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -2.0A; I_B= -0.1A			-1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -40V; I_E= 0			-1.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -4V; I_C= 0			-1.0	mA
h_{FE-1}	DC Current Gain	I_C= -0.1A ; V_{CE}= -2V	100		560	
h_{FE-2}	DC Current Gain	I_C= -3A ; V_{CE}= -2V	40			

◆ **h_{FE-1} Classifications**

R	S	T	U
100-200	140-280	200-400	280-560